

Schottky Barrier Diode

Lead free product

Halogen-free type

●Applications

Low current rectification and high speed switching

●Features

Extremely small surface mounting type. (SC-79/SOD523)

Extremely Fast Switching Speed

Extremely Low Forward Voltage 0.5 V (max) @ $I_F = 200$ mA

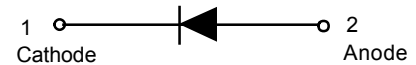
Low Reverse Current

●Construction

Silicon epitaxial planar

- We declare that the material of product compliance with RoHS requirements.

RB521S-30GH



DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
RB521S-30GH	5M	3000/Tape&Reel

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	30	V
Mean rectifying current	I_o	200	mA
Peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{sg}	-40~+125	$^\circ\text{C}$

*60Hz for 1cycle.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.50	V	$I_F = 200\text{mA}$
Reverse current	I_R	-	-	30	μA	$V_R = 10\text{V}$

Electrical characteristic curves(Ta=25°C)

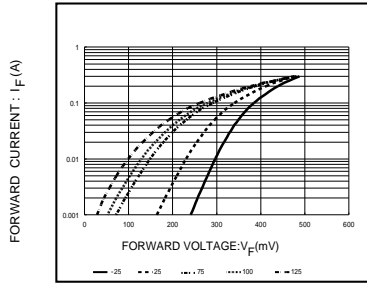


Fig. 1 Forward characteristics

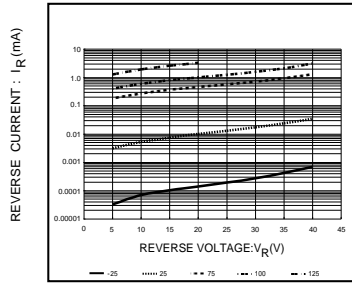


Fig. 2 Reverse characteristics

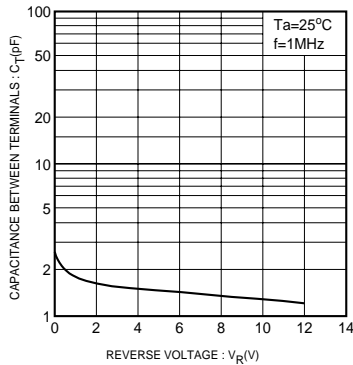
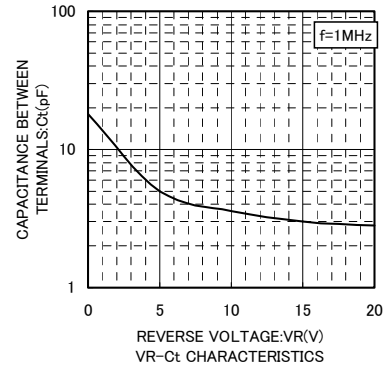


Fig. 3 Capacitance between terminals characteristics

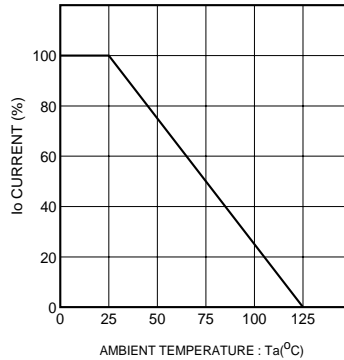
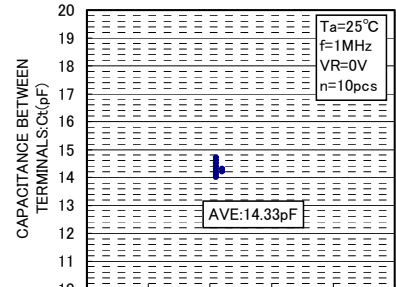
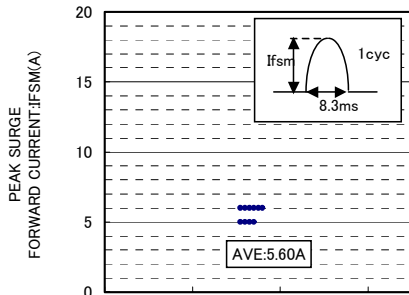


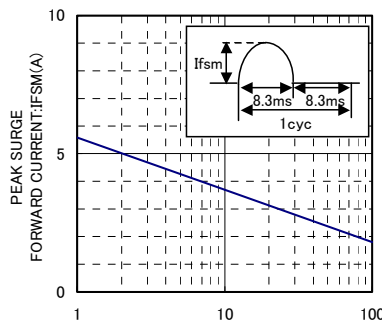
Fig. 4 Derating curve (mounting on glass epoxy PCBs)



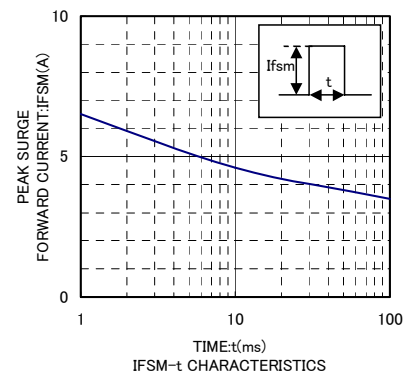
Ct DISPERSION MAP



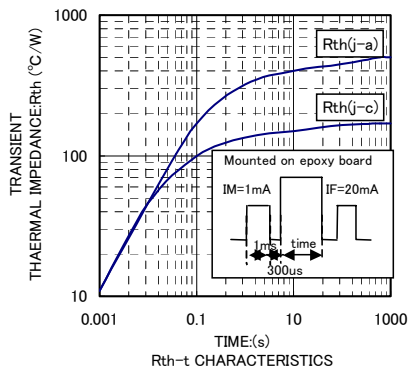
IFSM DISPERSION MAP



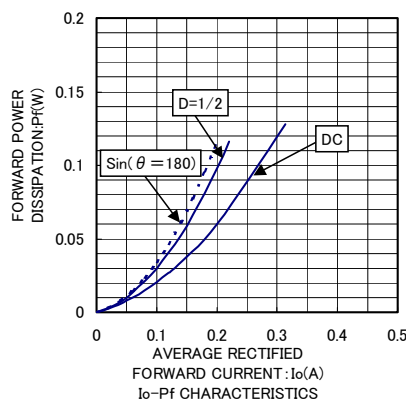
IFSM-CYCLE CHARACTERISTICS



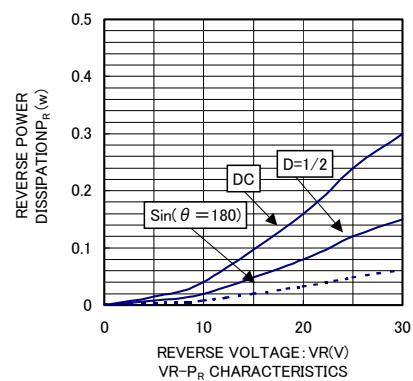
IFSM-t CHARACTERISTICS



Rth-t CHARACTERISTICS



Io-Pf CHARACTERISTICS



VR-PR CHARACTERISTICS